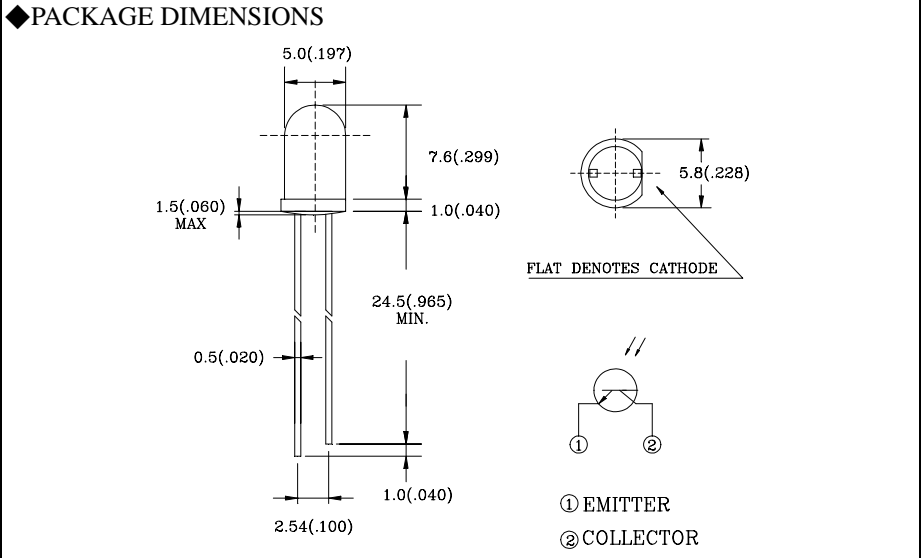




L-51ROPT1XX 5.0mm PHOTOTRANSISTOR



◆ABSOLUTE MAXIMUM RATING: (Ta=25°C)

Part No.	P _D (mw)	V _{(BR)CEO} (V)	Topr	Tstg
L-51ROPT1XX	10	30	-35°C to 85°C	-35°C to 85°C
PARAMETER	Power Dissipation	Reverse break down Voltage	Operating Temperature Range	Storage Temperature Range

Lead Soldering Temperature { 1.6mm (0.063 inch) From Body } 250°C ±5°C For 3 Seconds

◆ELECTRO-OPTICAL CHARACTERISTICS: (Ta=25°C)

Part No.	BV _{CEO} (V)			BV _E (V)			I _{CEO} (nA)			V _{CE(S)} (V)			tr/t _F (uS)			I _C (mA)			C _{CB} (pF)			Δλ (nm)			
	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	Min	Peak	Max	
L-51ROPT1C	30			5					100			0.4			15/15	1.8	2.4			6.4			400		1050
L-51ROPT1D1	30			5					100			0.4			15/15	1.7	2.2			6.4			900	940	
L-51ROPT1D2	30			5					100			0.4			15/15	1.7	2.2			6.4			800	870	
TEST CONDITION	I _C =100uA Ee=0mW/cm ²			I _E =100uA Ee=0mW/cm ²			V _{CE} = 20V Ee=0mW/cm ²			I _C = 2mA Ee=0.5mW/cm ²			V _{CE} = 5V I _C = 1mA RL= 1000Ω			V _{CE} = 5V Ee=0.1mW/cm ²			f = 1MHZ V _{CB} =3V Ee=0mW/cm ²						
PARAMETER	COLLECTOR-EMITTER BREAKDOWN VOLTAGE			EMITTER-COLLECTOR BREAKDOWN VOLTAGE			COLLECTOR DARK CURRENT			COLLECTOR-EMITTER SATURATION VOLTAGE			RISE/FALL TIME			ON STATE COLLECTOR CURRENT			COLLECTOR BASE CAPACITANCE			SPECTRAL SENSITIVITY WAVELENGTH			

D1,D2 = BLACK

- All dimension are in millimeter (inches).
- Tolerance is ±0.25mm(0.01”)unless otherwise specified.